

**Features**

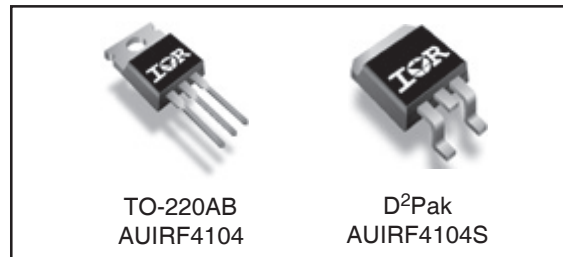
- Low On-Resistance
- Dynamic dV/dT Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified \*

**Description**

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.

HEXFET® Power MOSFET

	<b>V<sub>(BR)DSS</sub></b>	<b>40V</b>
	<b>R<sub>DS(on)</sub></b> <b>typ.</b>	<b>4.3mΩ</b>
		<b>max.</b>
	<b>I<sub>D</sub> (Silicon Limited)</b>	<b>120A</b> ⑨
	<b>I<sub>D</sub> (Package Limited)</b>	<b>75A</b>



**Absolute Maximum Ratings**

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T<sub>A</sub>) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	120 ⑨	A
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	84 ⑨	
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V (Wire Bond Limited)	75	
I <sub>DM</sub>	Pulsed Drain Current ①	470	
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Power Dissipation	140	W
	Linear Derating Factor	0.95	W/°C
V <sub>GS</sub>	Gate-to-Source Voltage	± 20	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (Thermally Limited) ②	120	mJ
E <sub>AS</sub> (tested )	Single Pulse Avalanche Energy Tested Value ③	220	
I <sub>AR</sub>	Avalanche Current ①	See Fig.12a, 12b, 15, 16	A
E <sub>AR</sub>	Repetitive Avalanche Energy ⑤		mJ
T <sub>J</sub>	Operating Junction and	-55 to + 175	°C
T <sub>STG</sub>	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting Torque, 6-32 or M3 screw ⑥	10 lbf•in (1.1N•m)	

**Thermal Resistance**

	Parameter	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case ⑦	—	1.05	°C/W
R <sub>θCS</sub>	Case-to-Sink, Flat Greased Surface	0.50	—	
R <sub>θJA</sub>	Junction-to-Ambient (PCB Mount)	—	40	

HEXFET® is a registered trademark of International Rectifier.

Note ① to ⑨ are on page 3

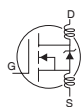
\*Qualification standards can be found at <http://www.irf.com/>

[www.irf.com](http://www.irf.com)

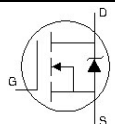
## Static Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	40	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.032	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	4.3	5.5	mΩ	$V_{GS} = 10V, I_D = 75A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$g_{fs}$	Forward Transconductance	63	—	—	V	$V_{DS} = 10V, I_D = 75A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 40V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 40V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -20V$

## Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)

$Q_g$	Total Gate Charge	—	68	100	nC	$I_D = 75A$
$Q_{gs}$	Gate-to-Source Charge	—	21	—		$V_{DS} = 32V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	27	—		$V_{GS} = 10V$ ③
$t_{d(on)}$	Turn-On Delay Time	—	16	—	ns	$V_{DD} = 20V$
$t_r$	Rise Time	—	130	—		$I_D = 75A$
$t_{d(off)}$	Turn-Off Delay Time	—	38	—		$R_G = 6.8\ \Omega$
$t_f$	Fall Time	—	77	—		$V_{GS} = 10V$ ③
$L_D$	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	—	7.5	—		
$C_{iss}$	Input Capacitance	—	3000	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	660	—		$V_{DS} = 25V$
$C_{rss}$	Reverse Transfer Capacitance	—	380	—		$f = 1.0MHz$
$C_{oss}$	Output Capacitance	—	2160	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz$
$C_{oss}$	Output Capacitance	—	560	—		$V_{GS} = 0V, V_{DS} = 32V, f = 1.0MHz$
$C_{oss\ eff.}$	Effective Output Capacitance	—	850	—		$V_{GS} = 0V, V_{DS} = 0V\ to\ 32V$ ④

## Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	75	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	470		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 75A, V_{GS} = 0V$ ③
$t_{rr}$	Reverse Recovery Time	—	23	35	ns	$T_J = 25^\circ\text{C}, I_F = 75A, V_{DD} = 20V$
$Q_{rr}$	Reverse Recovery Charge	—	6.8	10	nC	$di/dt = 100A/\mu s$ ③
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				

**Qualification Information†**

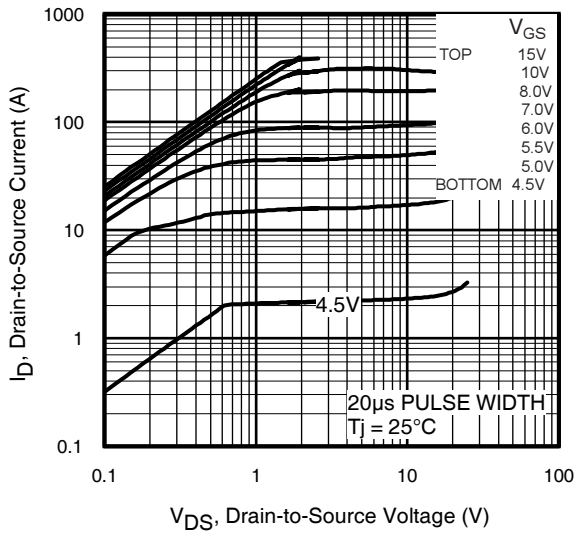
<b>Qualification Level</b>		Automotive (per AEC-Q101) ††	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
<b>Moisture Sensitivity Level</b>		TO-220AB	N/A
		D <sup>2</sup> PAK	MSL1
<b>ESD</b>	Machine Model	Class M4 AEC-Q101-002	
	Human Body Model	Class H1C AEC-Q101-001	
	Charged Device Model	Class C3 AEC-Q101-005	
<b>RoHS Compliant</b>		Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

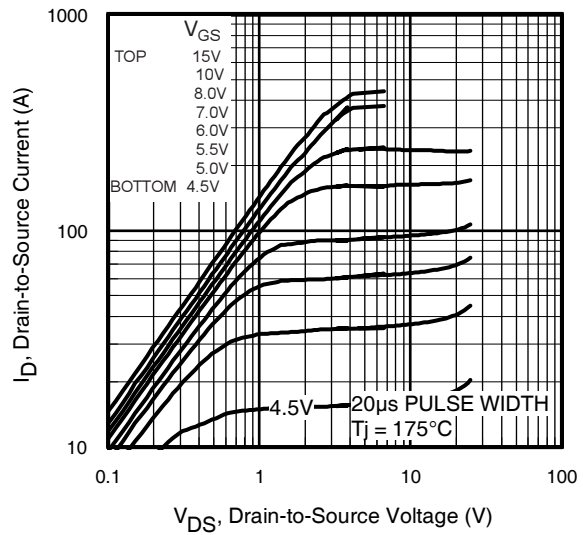
†† Exceptions to AEC-Q101 requirements are noted in the qualification report.

**Notes:**

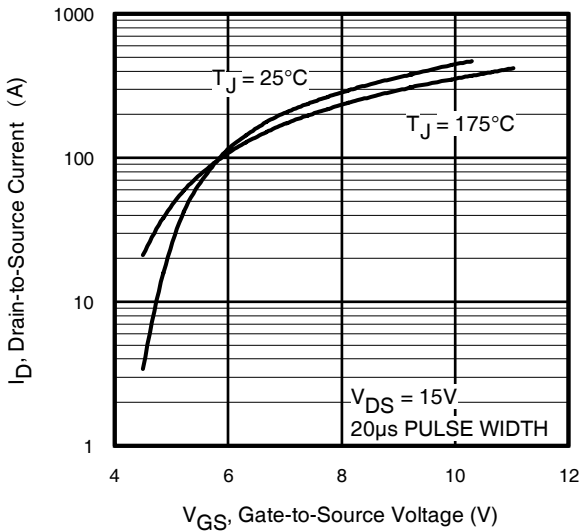
- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- ② Limited by  $T_{Jmax}$ , starting  $T_J = 25^{\circ}C$ ,  $L = 0.04mH$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 75A$ ,  $V_{GS} = 10V$ . Part not recommended for use above this value.
- ③ Pulse width  $\leq 1.0ms$ ; duty cycle  $\leq 2\%$ .
- ④  $C_{oss}$  eff. is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑤ This value determined from sample failure population, starting  $T_J = 25^{\circ}C$ ,  $L = 0.04mH$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 75A$ ,  $V_{GS} = 10V$
- ⑥ This is applied to D<sup>2</sup>Pak, when mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑦  $R_{\theta}$  is measured at  $T_J$  approximately 90°C.
- ⑧ This is only applied to TO-220AB package.
- ⑨ Calculated continuous current based on maximum allowable junction temperature. Bond wire current limit is 75A. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements. (Refer to AN-1140 <http://www.irf.com/technical-info/appnotes/an-1140.pdf>)



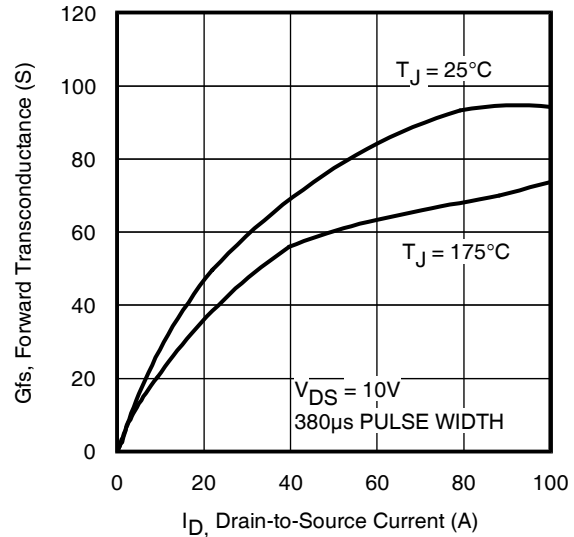
**Fig 1.** Typical Output Characteristics



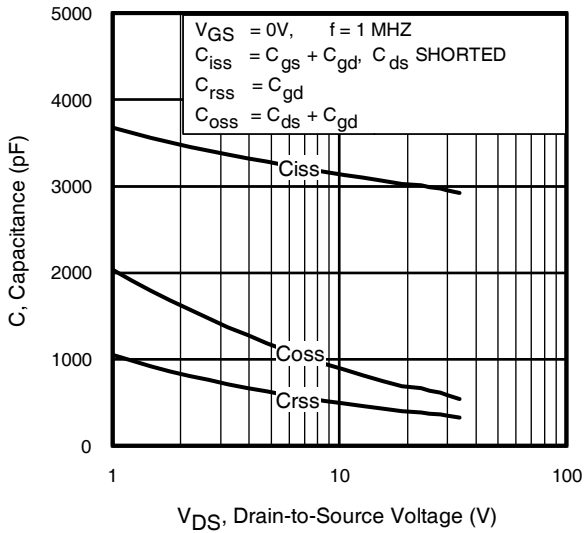
**Fig 2.** Typical Output Characteristics



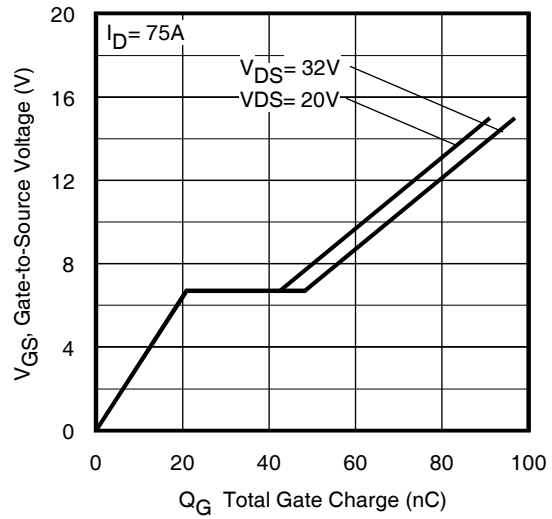
**Fig 3.** Typical Transfer Characteristics



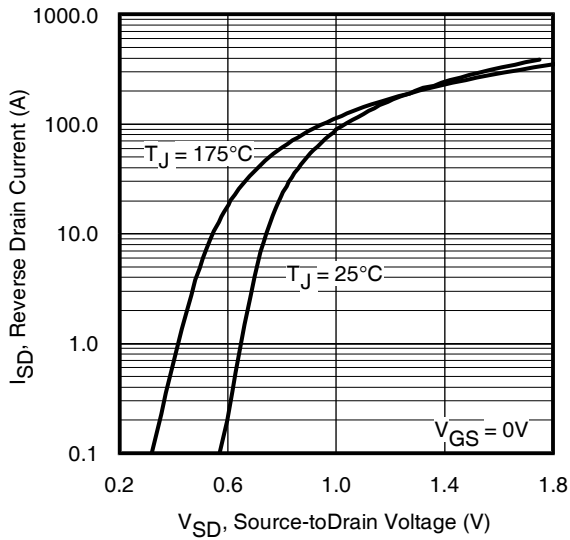
**Fig 4.** Typical Forward Transconductance Vs. Drain Current



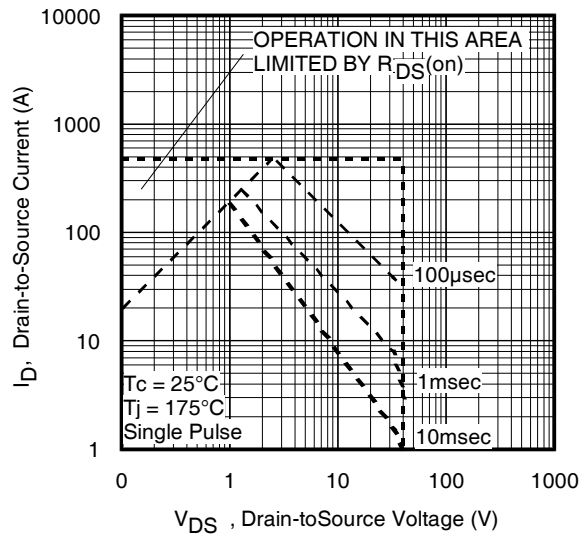
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



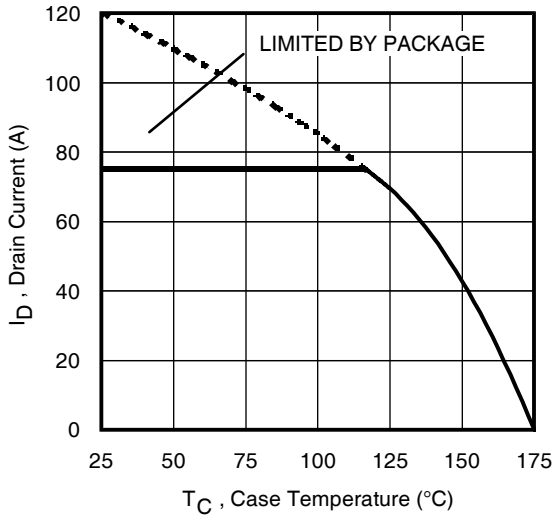
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



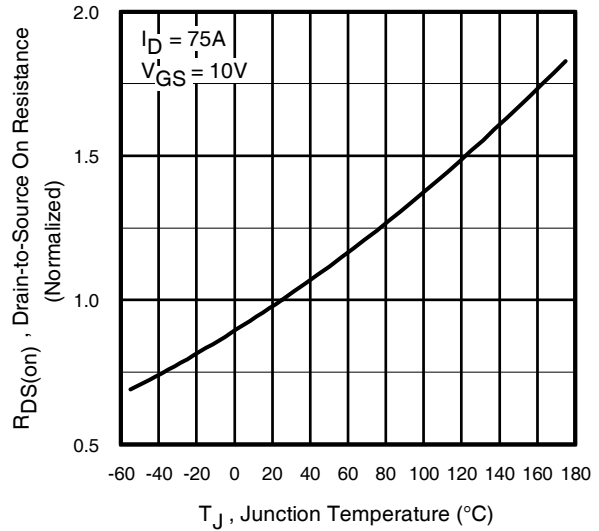
**Fig 7.** Typical Source-Drain Diode Forward Voltage



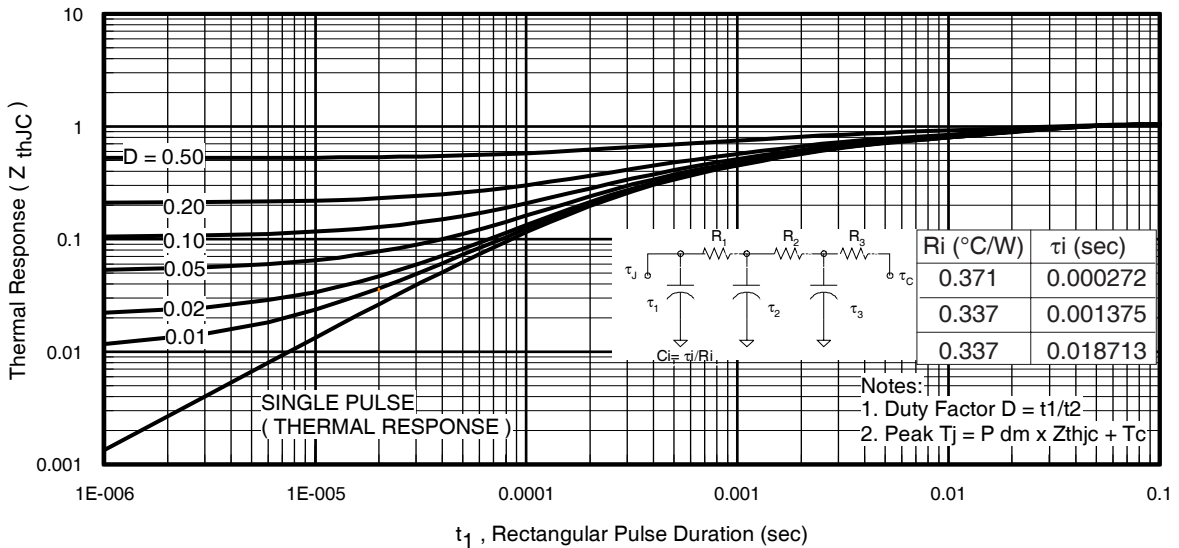
**Fig 8.** Maximum Safe Operating Area



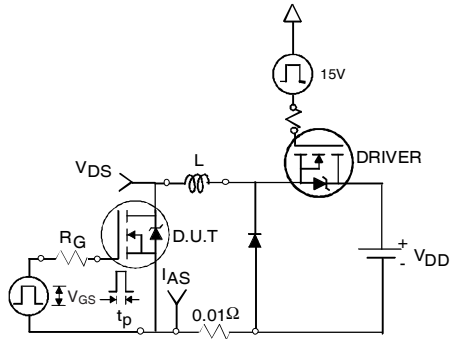
**Fig 9.** Maximum Drain Current Vs. Case Temperature



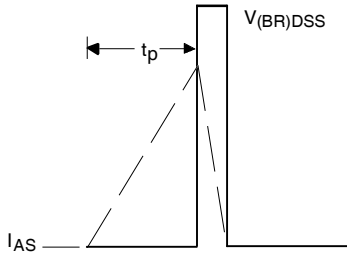
**Fig 10.** Normalized On-Resistance Vs. Temperature



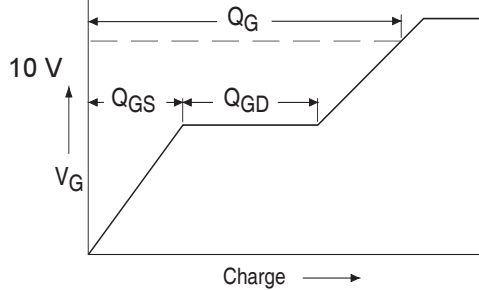
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



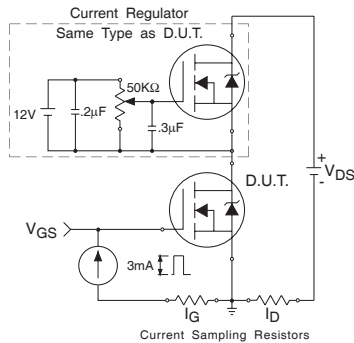
**Fig 12a.** Unclamped Inductive Test Circuit



**Fig 12b.** Unclamped Inductive Waveforms

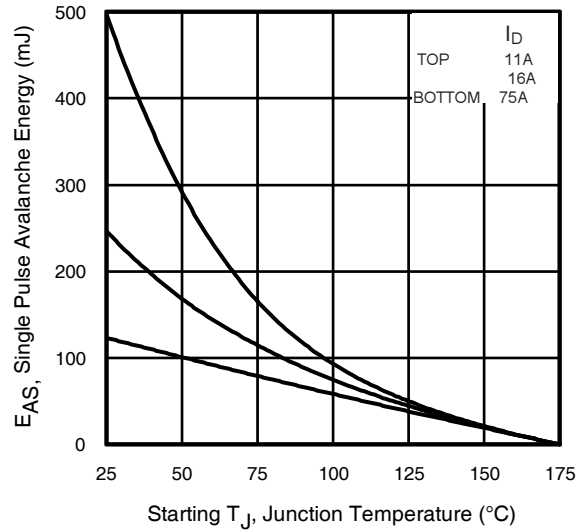


**Fig 13a.** Basic Gate Charge Waveform

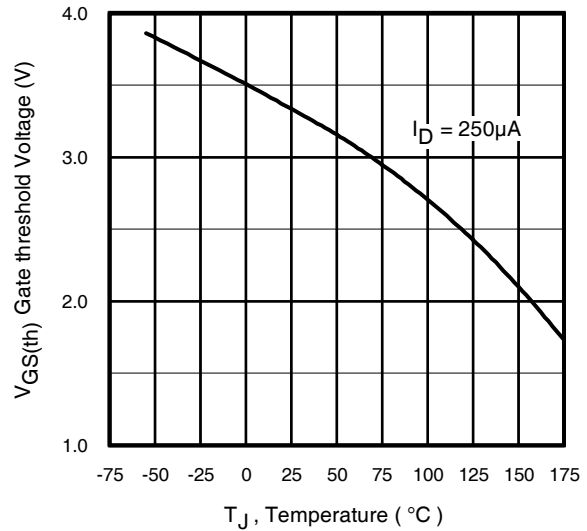


**Fig 13b.** Gate Charge Test Circuit

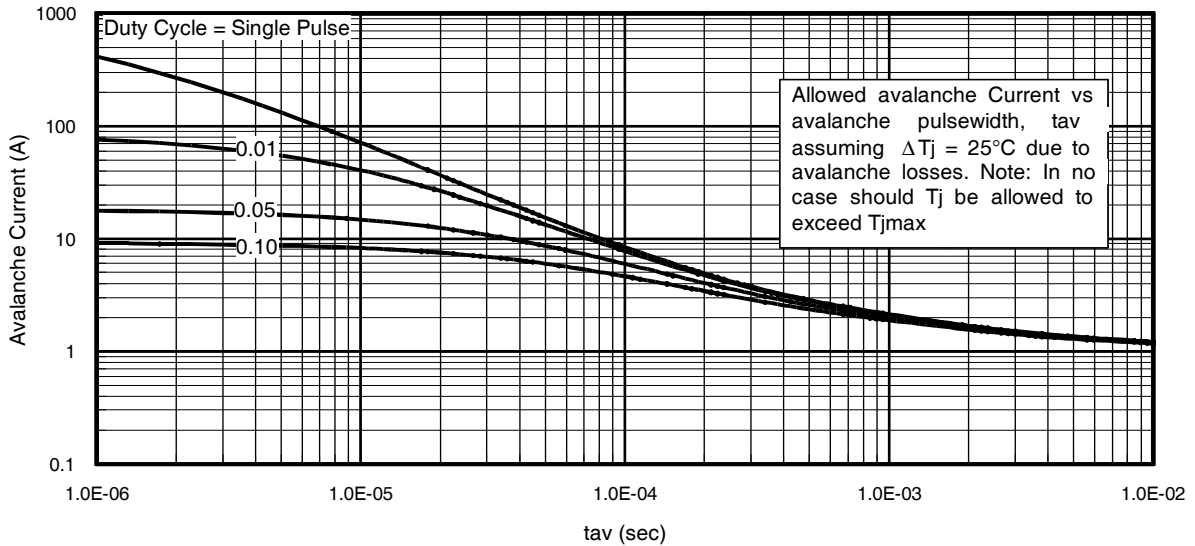
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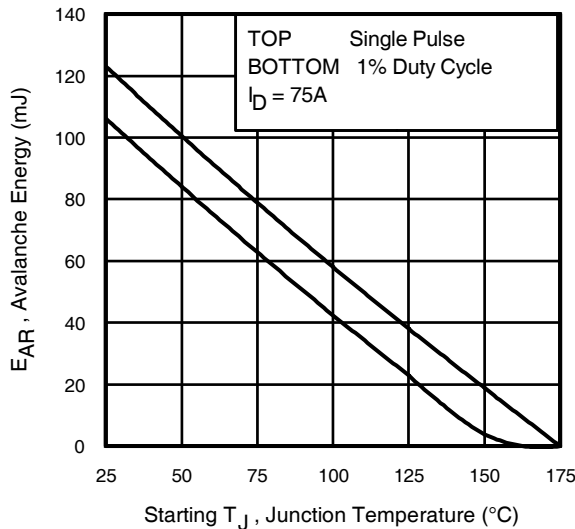
**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 14.** Threshold Voltage Vs. Temperature



**Fig 15.** Typical Avalanche Current Vs.Pulsewidth



**Fig 16.** Maximum Avalanche Energy Vs. Temperature

**Notes on Repetitive Avalanche Curves , Figures 15, 16:**  
**(For further info, see AN-1005 at [www.irf.com](http://www.irf.com))**

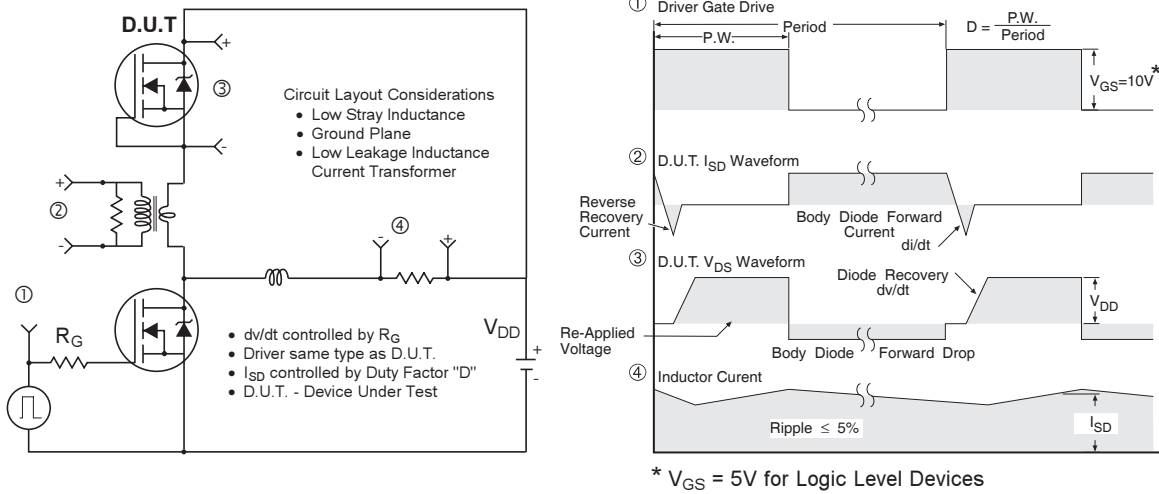
1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5.  $BV$  = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as 25°C in Figure 15, 16).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see figure 11)

$$P_{D(ave)} = 1/2 ( 1.3 \cdot BV \cdot I_{av} ) = \Delta T / Z_{thJC}$$

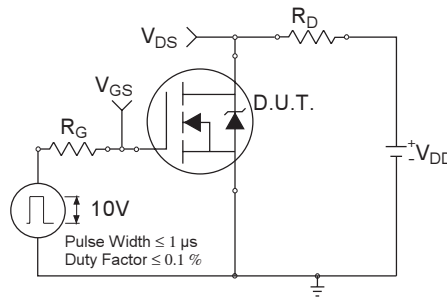
$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

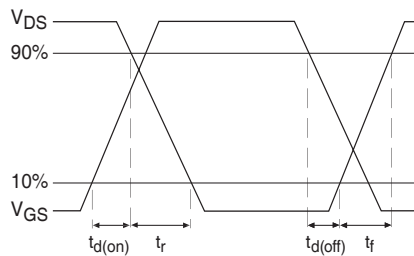




**Fig 17. Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET® Power MOSFETs**



**Fig 18a. Switching Time Test Circuit**

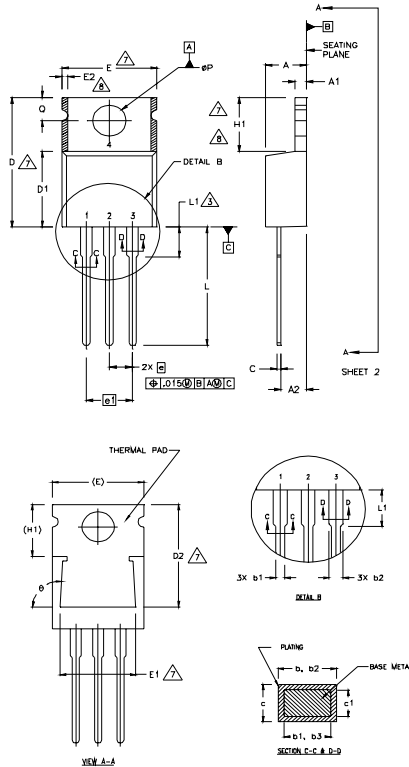


**Fig 18b. Switching Time Waveforms**

# AUIRF4104/S

## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



**NOTES:**

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 5 DIMENSION b1 & c1 APPLY TO BASE METAL ONLY.
- 6 CONTROLLING DIMENSION : INCHES.
- 7 THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
- 8 DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.

**LEAD ASSIGNMENTS**

- HERFEEI**  
 1- GATE  
 2- DRAIN  
 3- SOURCE

**IGBTs, CoPACK**

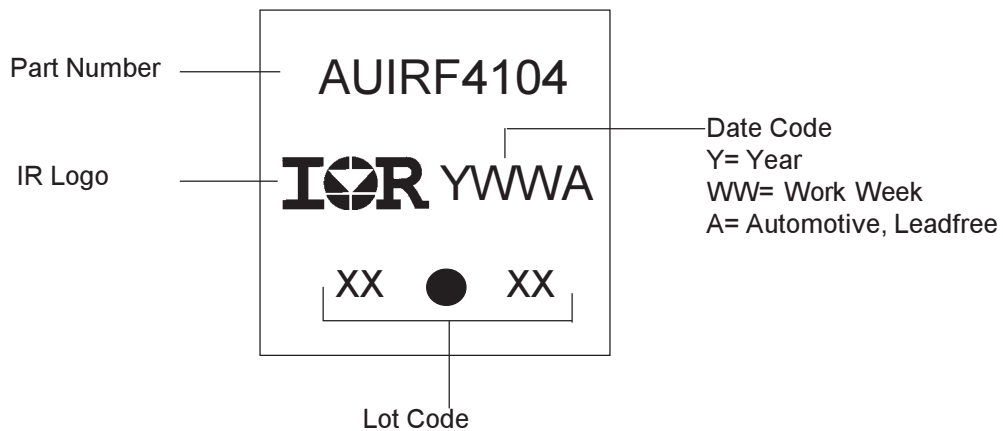
- 1- GATE  
 2- COLLECTOR  
 3- EMITTER

**DIODES**

- 1- ANODE/OPEN  
 2- CATHODE  
 3- ANODE

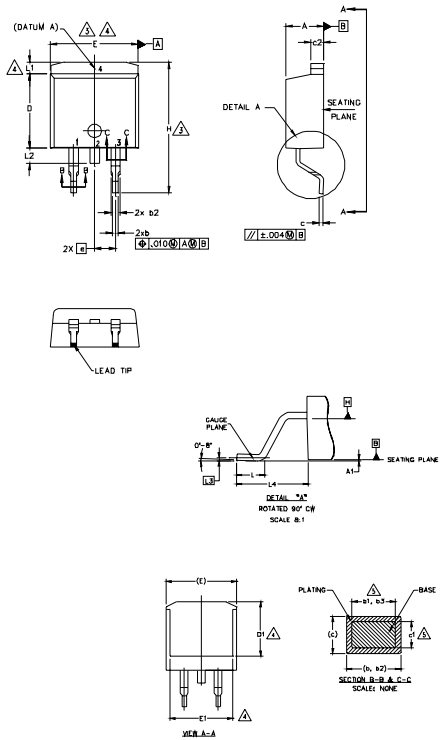
SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.82	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.04	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.96	.015	.038	5
b2	1.15	1.77	.045	.070	
b3	1.15	1.73	.045	.068	
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	12.19	12.88	.480	.507	7
E	9.66	10.66	.380	.420	4,7
E1	8.38	8.89	.330	.350	7
e	2.54 BSC		.100 BSC		
e1	5.08		.200 BSC		
H1	5.85	6.55	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	-	6.35	-	.250	
ØP	3.54	4.08	.139	.161	
O	2.54	3.42	.100	.135	
Ø	90°-93°		90°-93°		

## TO-220AB Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

## D<sup>2</sup>Pak Package Outline (Dimensions are shown in millimeters (inches))



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
  2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
  3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
  4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
  5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
  6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
  7. CONTROLLING DIMENSION: INCH.
  8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	5
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	
D1	6.86	-	.270	-	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	-	.245	-	4
e	2.54	BSC	.100	BSC	4
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	-	1.65	-	.066	
L2	1.27	1.78	-	.070	
L3	0.25	BSC	.010	BSC	
L4	4.78	5.28	.188	.208	

### LEAD ASSIGNMENTS

#### HEXFET

- 1.- GATE
- 2, 4.- DRAIN
- 3.- SOURCE

#### IGBTs, CoPACK

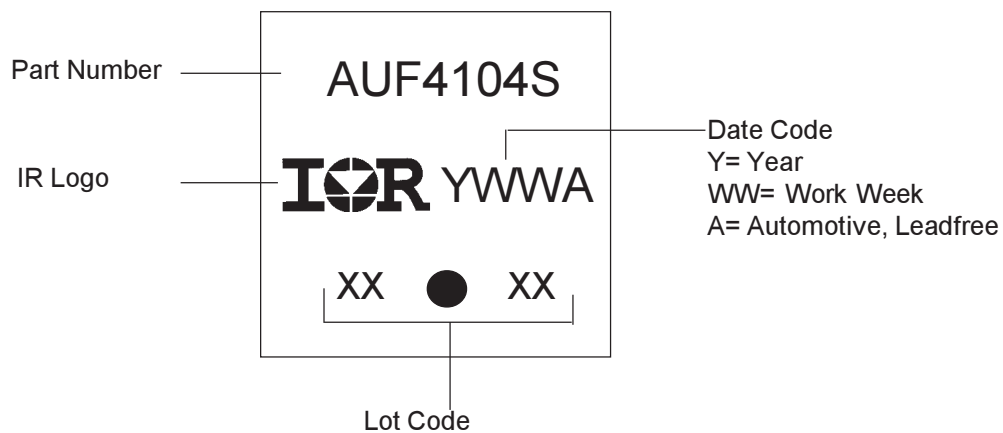
- 1.- GATE
- 2, 4.- COLLECTOR
- 3.- EMITTER

#### DIODES

- 1.- ANODE \*
- 2, 4.- CATHODE
- 3.- ANODE

\* PART DEPENDENT.

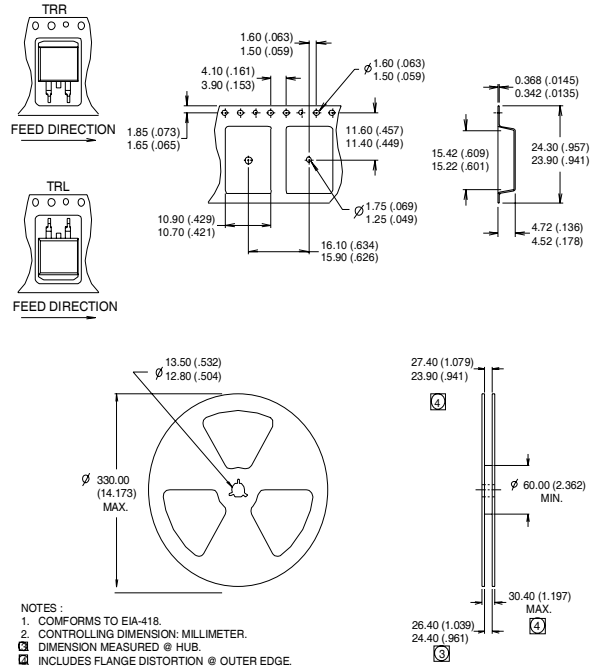
## D<sup>2</sup>Pak Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>  
www.irf.com

# AUIRF4104/S

## D<sup>2</sup>Pak Tape & Reel Information



**TO-220AB package is not recommended for Surface Mount Application.**

## Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRF4104	TO-220	Tube	50	AUIRF4104
AUIRF4104S	D2Pak	Tube	50	AUIRF4104S
AUIRF4104S		Tape and Reel Left	800	AUIRF4104STRL
AUIRF4104S		Tape and Reel Right	800	AUIRF4104STRR

## IMPORTANT NOTICE

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<http://www.irf.com/technical-info/>

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## Revision History

Date	Comments
2/5/2010	Revised with new AU template:
	1)Add sentence below Absolute Max Rating
	2)Update ESD by using ESD data and table from Anika
	3)Update Part Marking drawing
	4) Add Order Info table
	5) Add Revision History